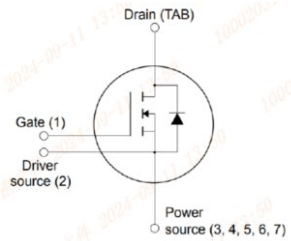
1200V 32mΩ Silicon Carbide Power MOSFET

Features

- AEC-Q101 qualified
- High blocking voltage with low on-resistance
- High switching speed with low capacitance
- Very fast and robust intrinsic body diode with low reverse recovery
- Very low switching losses
- Excellent avalanche ruggedness
- RoHS compliant

Benefits

- Greater system efficiency
- Reduced cooling requirements
- Increased power density
- Increased system switching frequency
- Easy to parallel and simple to drive



Package Type: SAPKG-9L

Potential Applications

- Solar inverters
- Uninterrupted power supplies
- Switch mode power supplies
- Motor drives

AEC-Q101

Description

The Sanan Semiconductor 1200V/32mΩ silicon carbide power MOSFET uses advanced SiC MOSFET technology with low on-resistance, low switching losses, and a high operation temperature of 175℃. It is suitable for use in high frequency circuits and provides a reduction in overall system size, increased efficiency and increased switching frequency. It has been widely used in applications including solar inverters, uninterrupted power supplies, switch mode power supplies, and motor drives. Using RoHS compliant components and being AEC-Q101 qualified, it is qualified for use in industrial application.

Product Specifications

Device	V_{DS}	I_D (25℃)	$R_{(DS)on}$	Marking
AMS1200032V2	1200V	59A	32mΩ	MS1200032V2

CONTENTS

Table 1. Maximum Ratings

(T_C = 25℃, unless otherwise specified)

Parameter	Symbol	Value	Unit	Test conditions
Drain-source voltage	V_{DSmax}	1200	V	V_{GS} = 0V, I_D = 100μA
Gate-source voltage, max. transient voltage	V_{GSmax}	-10/+25		$t_p \leq$ 0.5us, D < 1%
Gate-source voltage, max. static voltage	V_{GSmax}	-8/+22		
Gate-source voltage	V_{GSop}	-5/+18		Recommended operation values,
Continuous drain current	I_D	59	A	V_{GS} = 18V
		42		V_{GS} = 18V, T_C = 100℃
Pulsed drain current	$I_{D(pulse)}$	148	A	Pulse width t_p limited by T_{jmax}
Power dissipation	P_{tot}	278	W	
Operating junction temperature	T_j	-55~175	℃	
Storage temperature	T_{stg}	-55~175	℃	
Soldering temperature	T_L	260	℃	1.6mm from case for 10s

Table 2. Thermal Resistances

Parameter	Symbol	Values			Unit	Test condition
		Min.	Typ.	Max.		
Thermal resistance from junction to case	$R_{th(j-c)}$	/	0.45	/	℃/W	

Table 3. Static Electrical Characteristics

(T_j = 25℃, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	1200	/	/	V	V_{GS} = 0V, I_D = 100μA
Gate threshold voltage	$V_{GS(th)}$	1.8	3.0	4.2		V_{DS} = V_{GS}, I_D = 10mA
		/	2.1	/		V_{DS} = V_{GS}, I_D = 10mA, T_j = 175℃
Drain-source leakage current	I_{DSS}	/	1	150	μA	V_{DS} = 1200V, V_{GS} = 0V
Gate-source leakage current	I_{GSS}	/	1	250	nA	V_{GS} = 18V, V_{DS} = 0V
Drain-source on-state resistance	$R_{DS(on)}$	/	37	/	mΩ	V_{GS} = 15V, I_D = 40A
		/	32	42		V_{GS} = 18V, I_D = 40A
		/	56	/		V_{GS} = 18V, I_D = 40A, T_j = 175℃
Transconductance	g_{fs}	/	30	/	S	V_{DS} = 20V, I_D = 40A
		/	25	/		V_{DS} = 20V, I_D = 40A, T_j = 175℃
Internal gate resistance	$R_{g(int)}$	/	4.2	/	Ω	f = 1MHz, V_{AC} = 25mV

Table 4. Dynamic Electrical Characteristics

(T_j = 25℃, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	/	2090	/	pF	V_{GS} = 0V, V_{DS} = 1000V, f = 1MHz, V_{AC} = 25mV
Output capacitance	C_{oss}	/	86	/		
Reverse transfer capacitance	C_{rss}	/	2	/		
C_{OSS} stored energy	E_{oss}	/	35	/	μJ	
Gate to source charge	Q_{GS}	/	30	/	nC	V_{DD} = 800V, V_{GS} = -5/+18V, I_D = 40A, I_{GS} = 1mA
Gate to drain charge	Q_{GD}	/	27	/		
Total gate charge	Q_G	/	91	/		

Table 5. Switching Characteristics

(T_j = 25℃, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
Turn-on delay time	$t_{d(on)}$	/	12	/	ns	V_{DD} = 800V, V_{GS} = -5/+18V, I_D = 40A, $R_{G(ext)}$ = 2.4Ω, L = 110μH
Rise time	t_r	/	16	/		
Turn-off delay time	$t_{d(off)}$	/	28	/		
Fall time	t_f	/	6	/		
Turn-on switching energy	E_{on}	/	279	/	μJ	
Turn-off switching energy	E_{off}	/	96	/		
Turn-on delay time	$t_{d(on)}$	/	10	/	ns	V_{DD} = 800V, V_{GS} = -5/+18V, I_D = 40A, $R_{G(ext)}$ = 2.4Ω, L = 110μH, T_j = 175℃
Rise time	t_r	/	15	/		
Turn-off delay time	$t_{d(off)}$	/	34	/		
Fall time	t_f	/	6	/		
Turn-on switching energy	E_{on}	/	245	/	μJ	
Turn-off switching energy	E_{off}	/	111	/		

Table 6. Reverse SiC Diode Characteristics

(T_j = 25℃, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	/	4.5	/	V	V_{GS} = -5V, I_{SD} = 40A
		/	3.9	/		V_{GS} = -5V, I_{SD} = 40A, T_j = 175°C
Continuous diode forward current	I_S	/	/	59	A	T_C = 25℃
Diode pulse current	$I_{S,\ pulse}$	/	/	148	A	V_{GS} = -5V, pulse width t_p limited by T_{jmax}
Reverse recovery time	t_{rr}	/	12	/	ns	V_{GS} = -5V, I_{SD} = 40A, V_R = 800V, di_f/dt =2.95kA/μs
Reverse recovery charge	Q_{rr}	/	0.24	/	μC	
Peak reverse recovery current	I_{rrm}	/	34	/	A	
Reverse recovery time	t_{rr}	/	21	/	ns	V_{GS} = -5V, I_{SD} = 40A, V_R = 800V, T_j = 175°C , di_f/dt =3.05kA/μs
Reverse recovery charge	Q_{rr}	/	0.78	/	μC	
Peak reverse recovery current	I_{rrm}	/	59	/	A	

Electrical Characteristic Diagrams

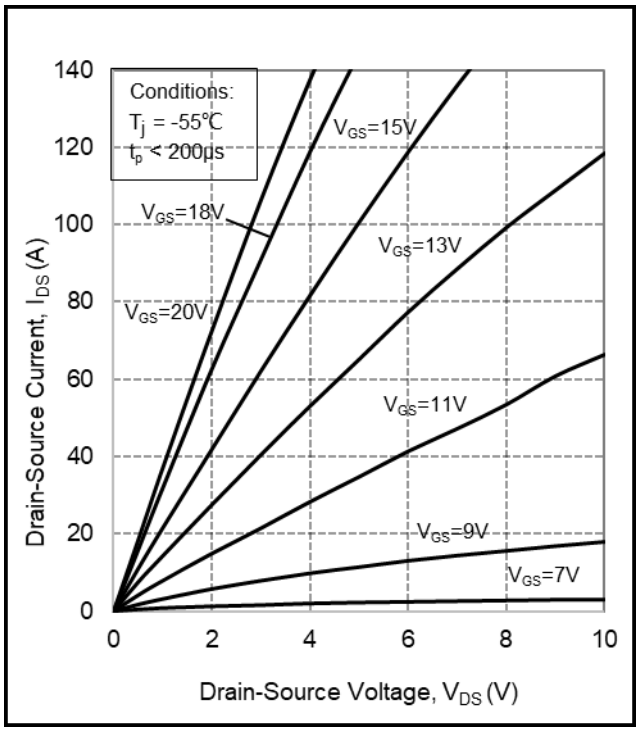


Figure 1. Output characteristics at T_j = -55℃

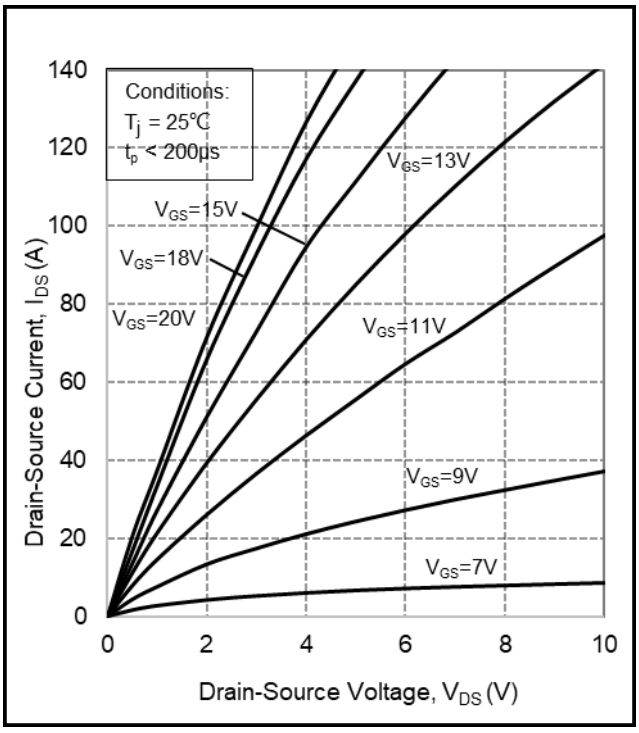


Figure 2. Output characteristics at T_j = 25℃

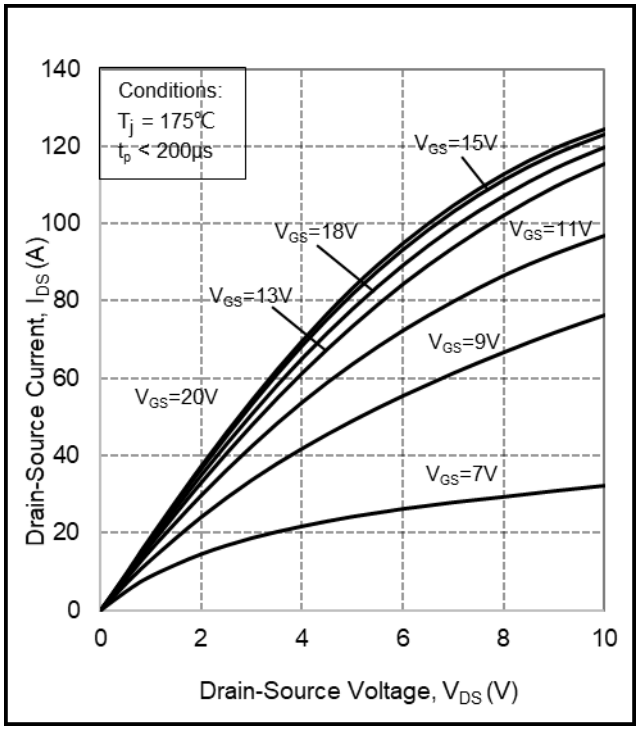


Figure 3. Output characteristics at T_j = 175℃

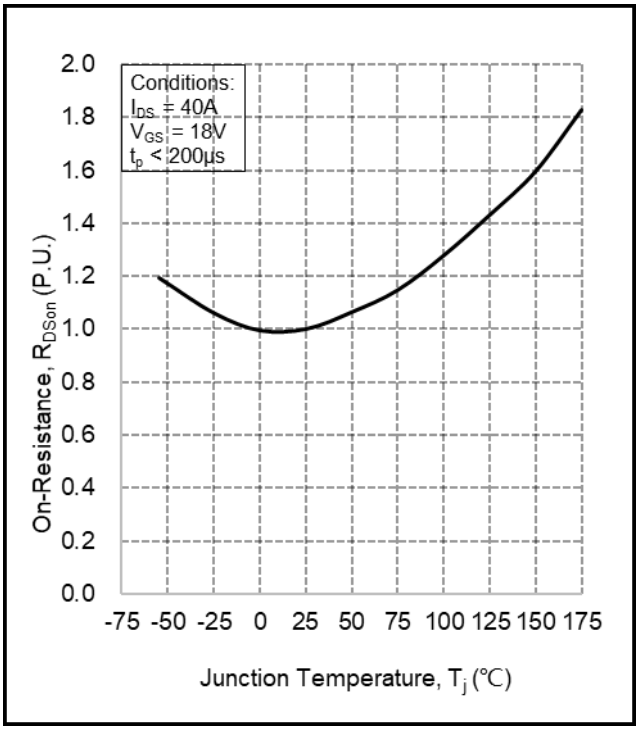


Figure 4. Normalized on-resistance vs. temperature

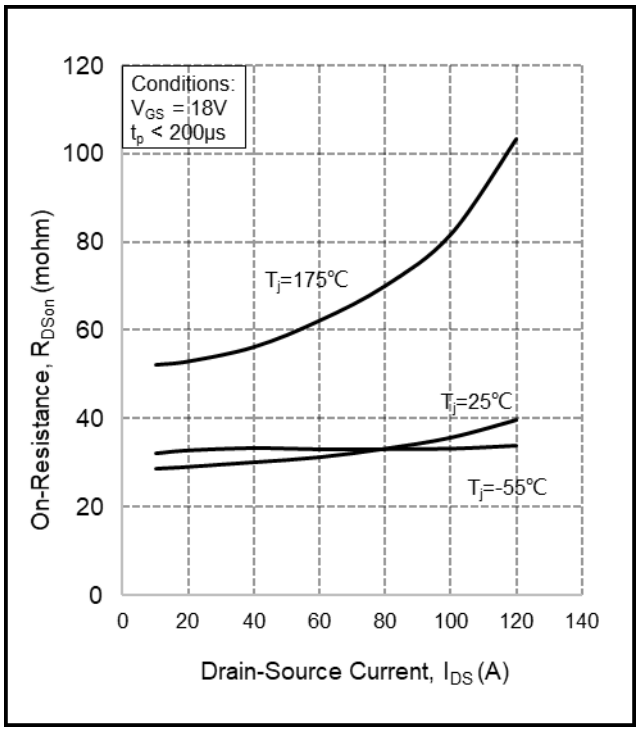


Figure 5. On-resistance vs. drain current for various temperatures

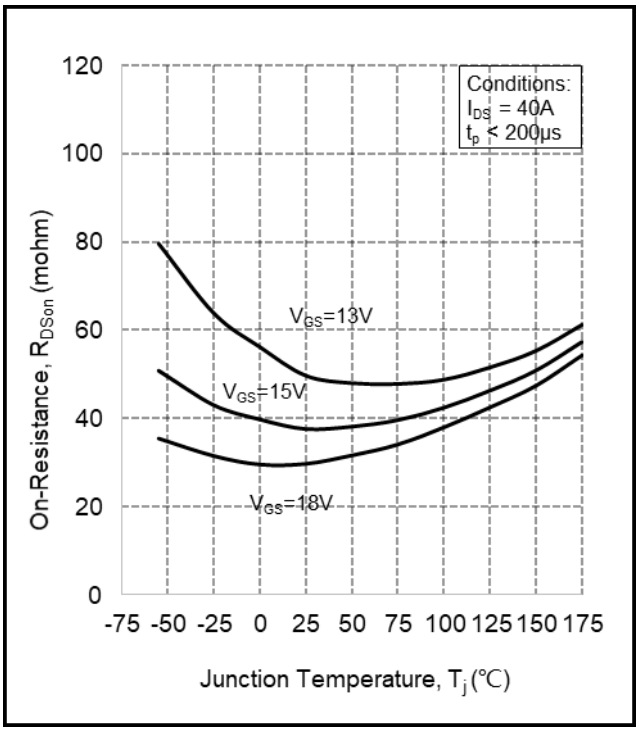


Figure 6. On-resistance vs. temperature for various gate voltages

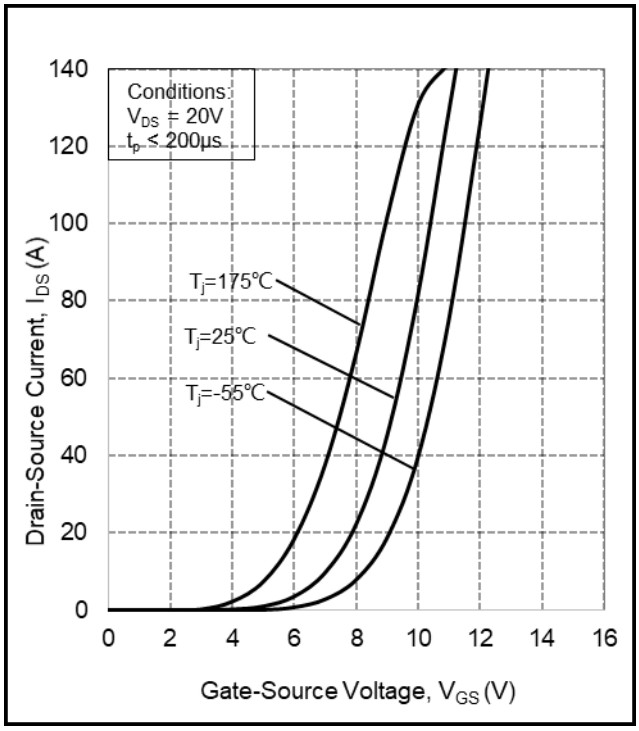


Figure 7. Transfer characteristic for various junction temperatures

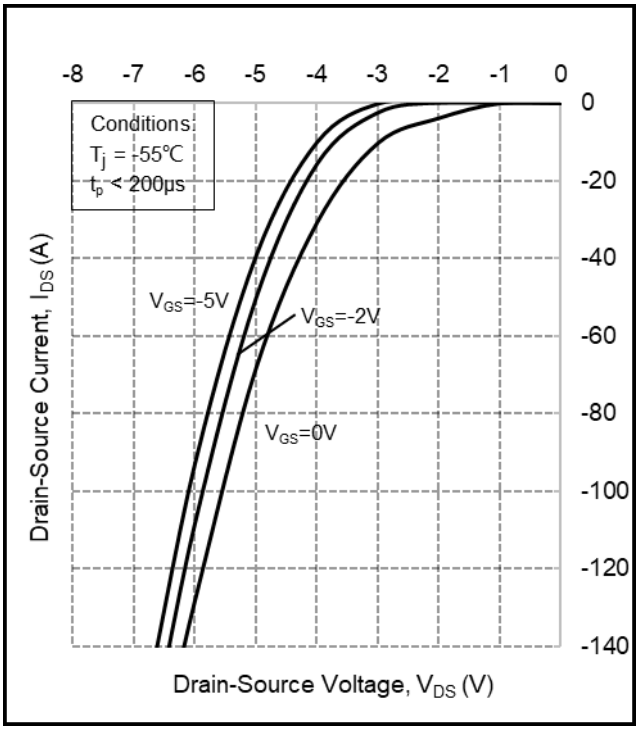


Figure 8. Body diode characteristic at T_j = -55℃

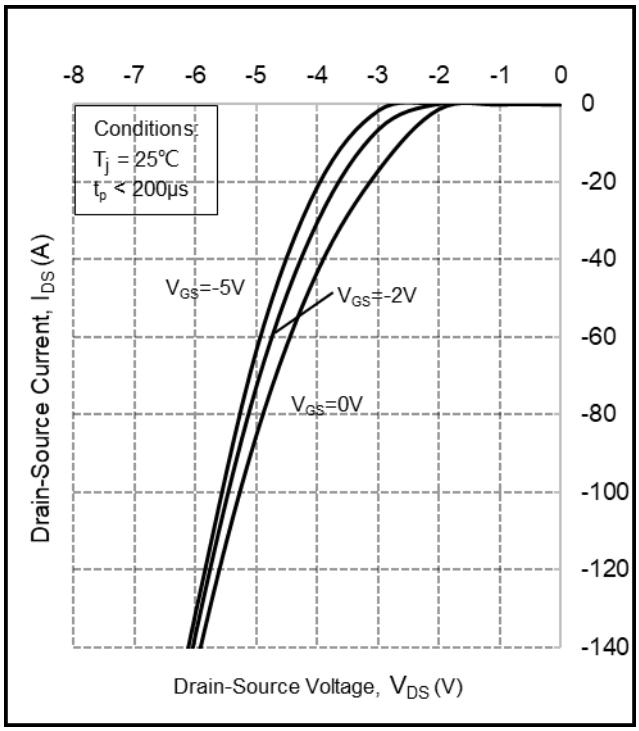


Figure 9. Body diode characteristic at T_j = 25℃

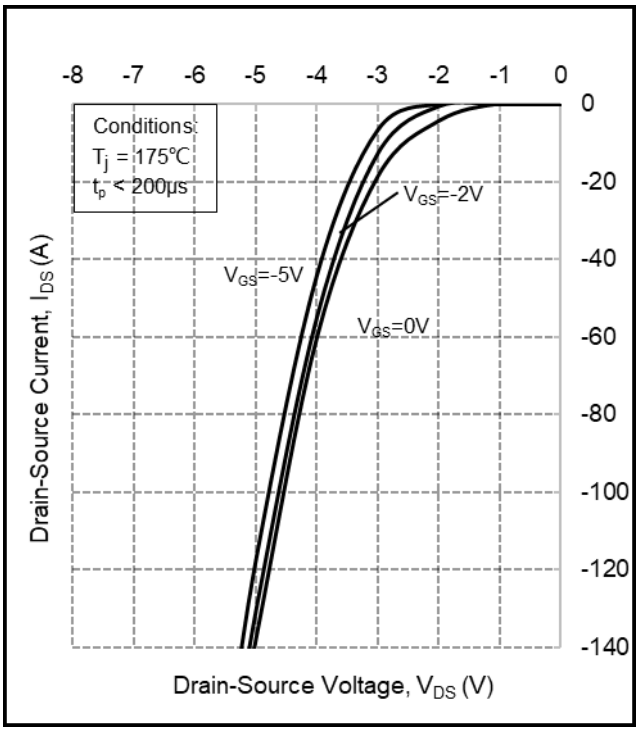


Figure 10. Body diode characteristic at T_j = 175℃

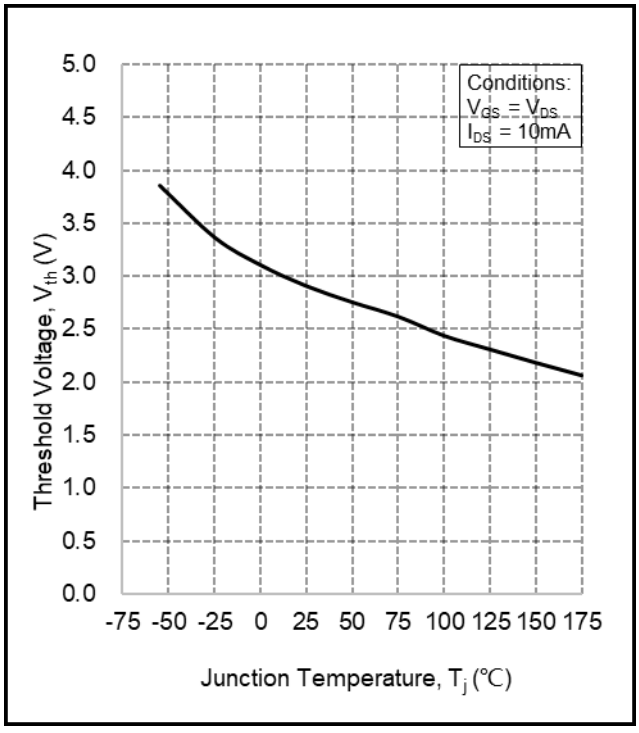


Figure 11. Threshold voltage vs. temperature

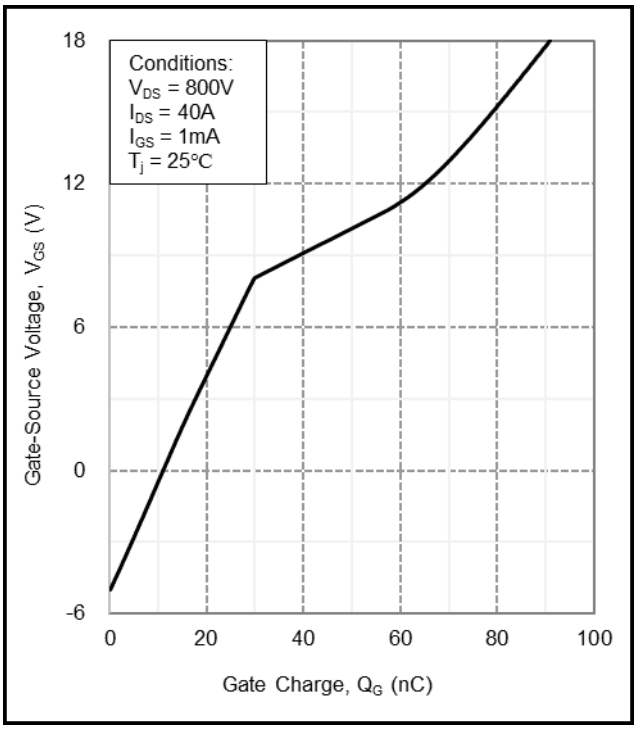


Figure 12. Gate charge characteristics

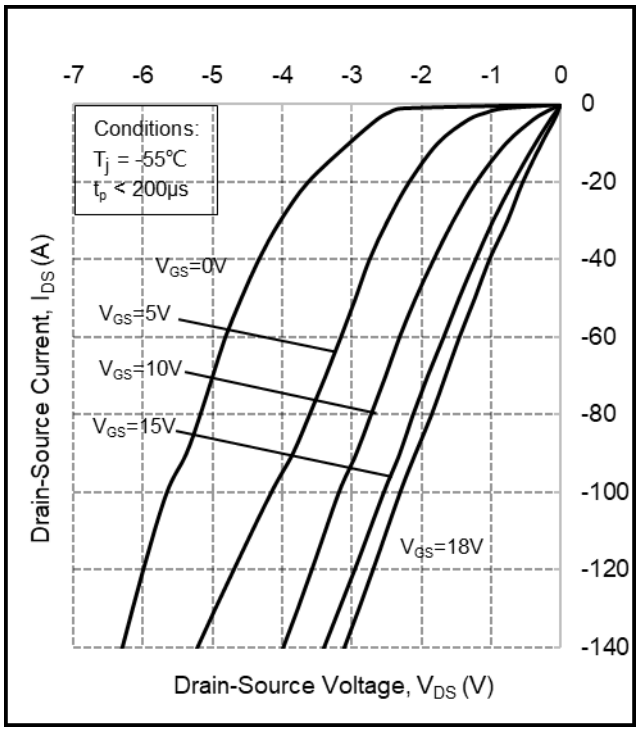


Figure 13. 3rd quadrant characteristic at T_j = -55℃

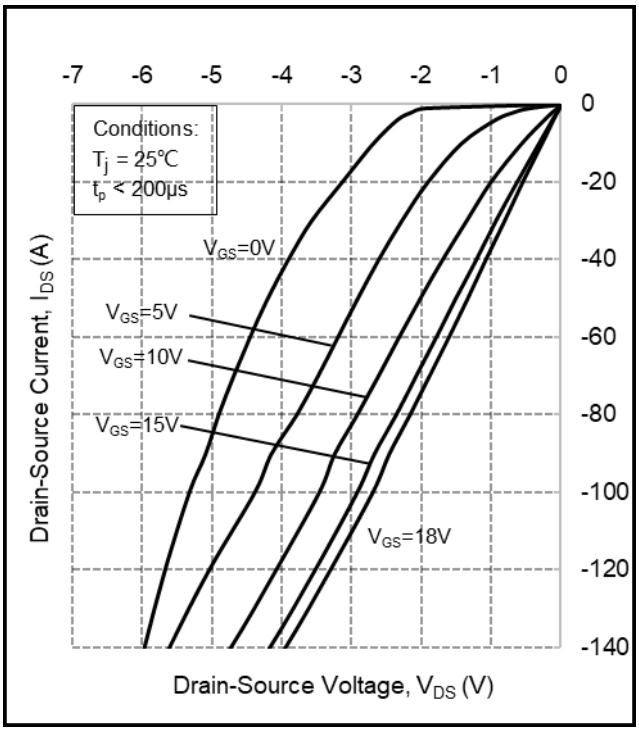


Figure 14. 3rd quadrant characteristic at T_j = 25℃

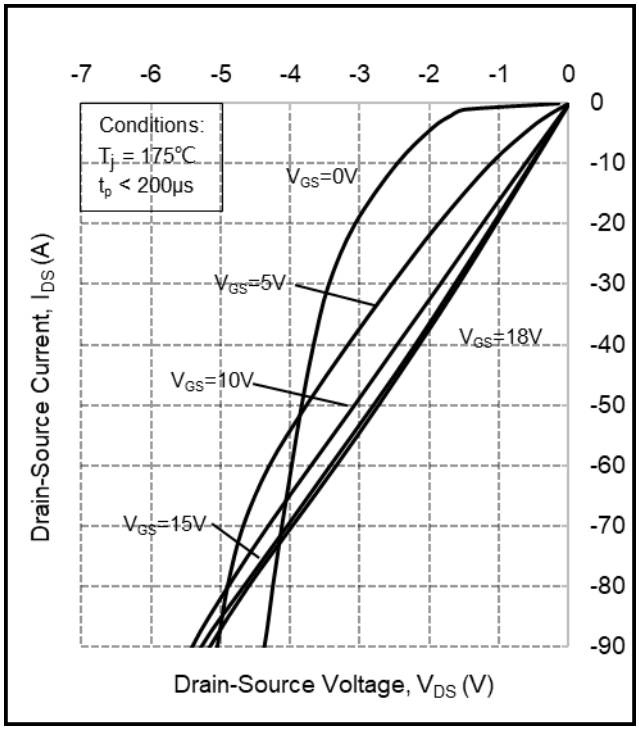


Figure 15. 3rd quadrant characteristic at T_j = 175℃

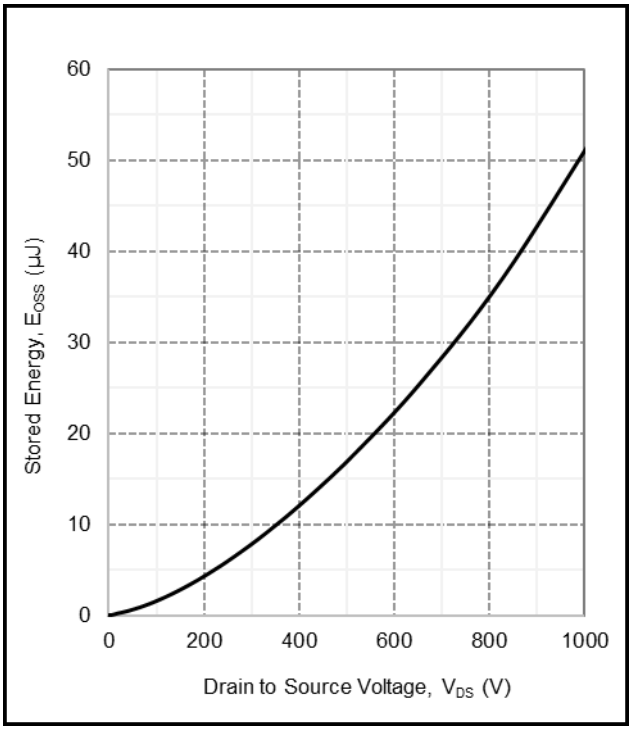


Figure 16. Output capacitor stored energy

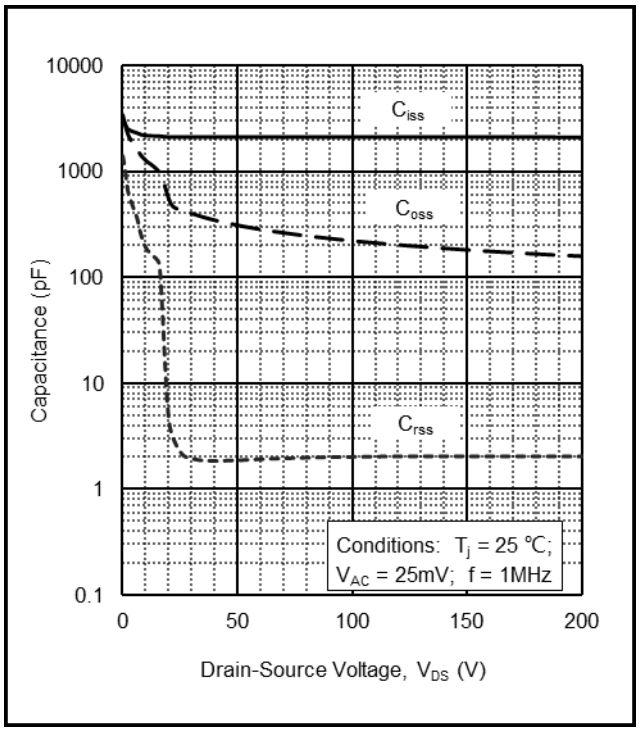


Figure 17. Capacitance vs. drain-source voltage (0 - 200V)

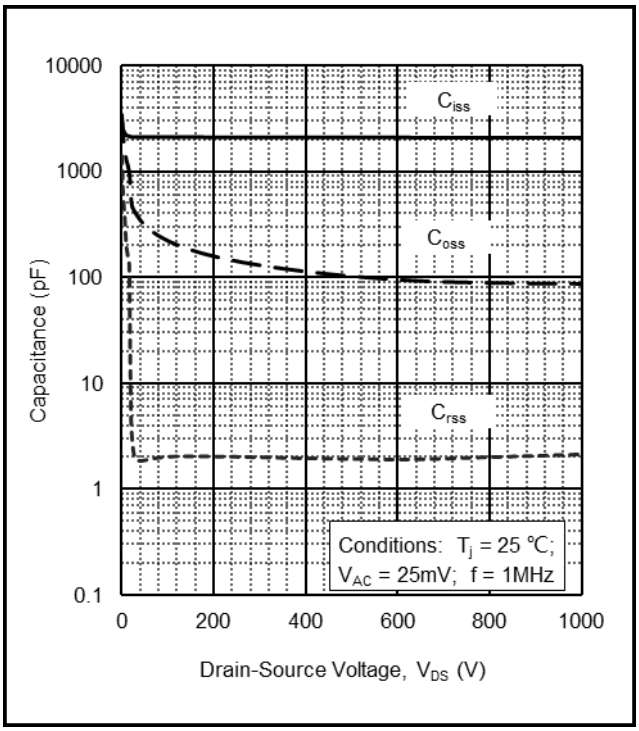


Figure 18. Capacitance vs. drain-source voltage (0 - 1000V)

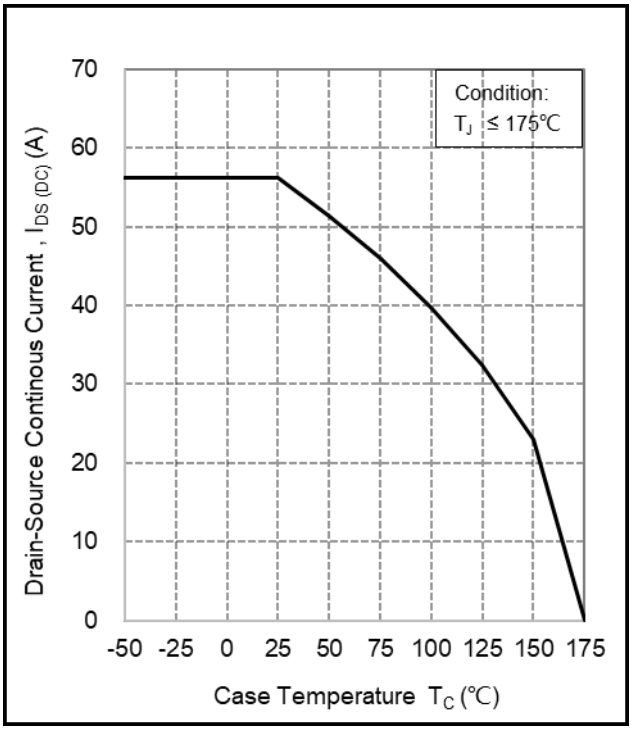


Figure 19. Continuous drain current derating vs. temperature

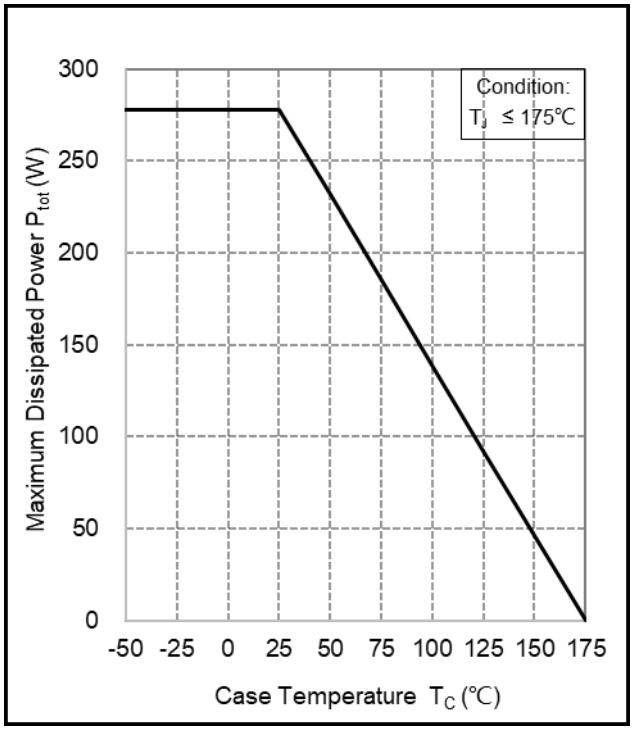


Figure 20. Maximum power dissipation derating vs. temperature

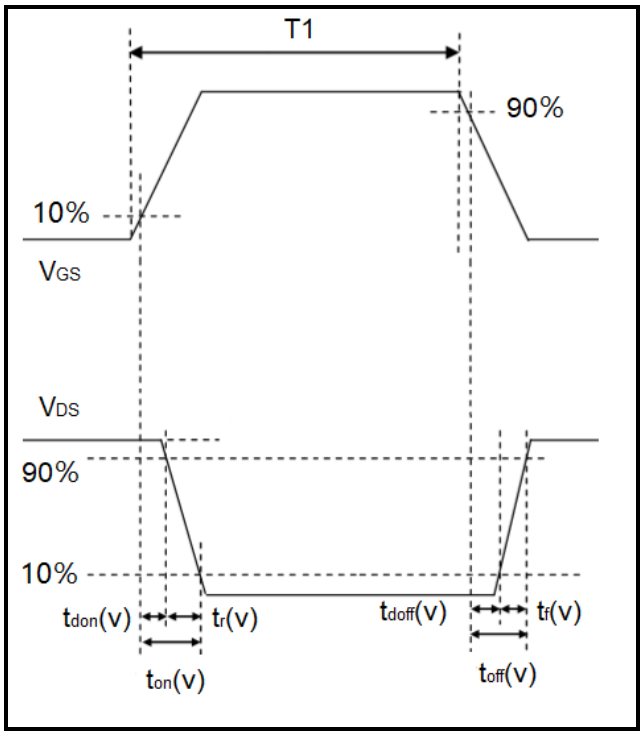


Figure 21. Switching times definition

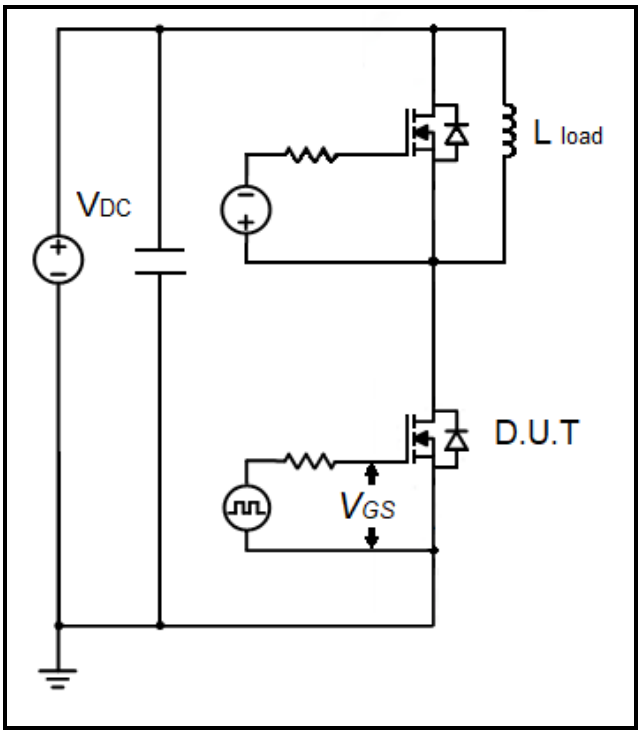
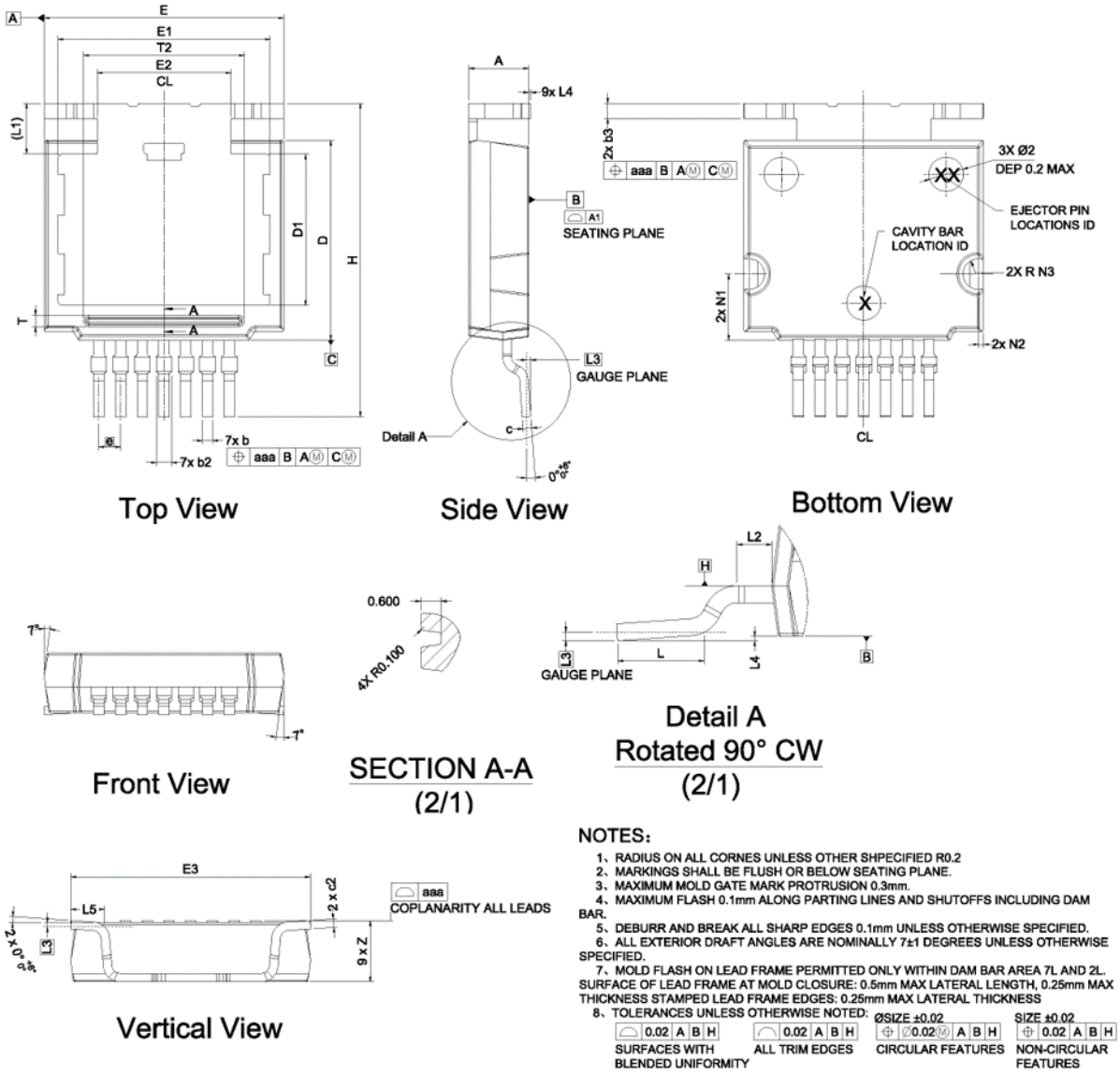


Figure 22. Clamped inductive switching waveform test circuit

Package Information



NOTES:

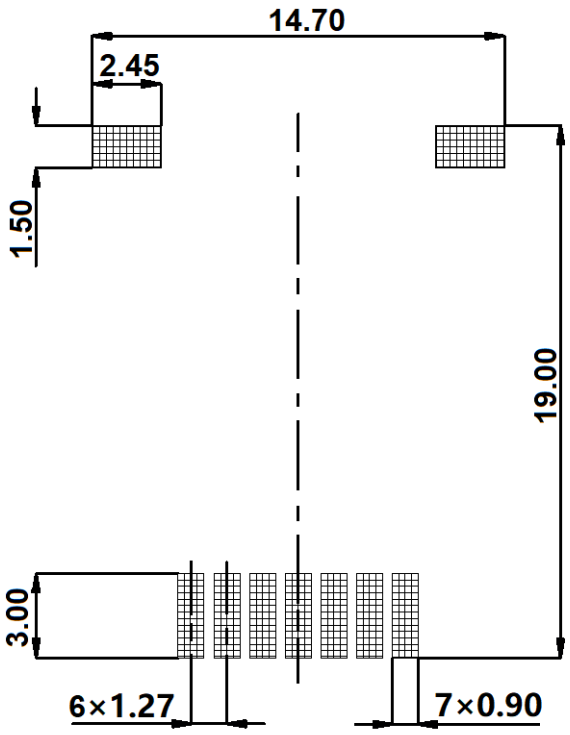
1、RADIUS ON ALL CORNES UNLESS OTHER SHPECIFIED R0.2
2、MARKINGS SHALL BE FLUSH OR BELOW SEATING PLANE.
3、MAXIMUM MOLD GATE MARK PROTRUSION 0.3mm.
4、MAXIMUM FLASH 0.1mm ALONG PARTING LINES AND SHUTOFFS INCLUDING DAM BAR.
5、DEBURR AND BREAK ALL SHARP EDGES 0.1mm UNLESS OTHERWISE SPECIFIED.
6、ALL EXTERIOR DRAFT ANGLES ARE NOMINALLY 7±1 DEGREES UNLESS OTHERWISE SPECIFIED.
7、MOLD FLASH ON LEAD FRAME PERMITTED ONLY WITHIN DAM BAR AREA 7L AND 2L. SURFACE OF LEAD FRAME AT MOLD CLOSURE: 0.5mm MAX LATERAL LENGTH, 0.25mm MAX THICKNESS STAMPED LEAD FRAME EDGES: 0.25mm MAX LATERAL THICKNESS
8、TOLERANCES UNLESS OTHERWISE NOTED:

0.02 A B H	0.02 A B H	ØSIZE ±0.02 Ø0.02Ⓜ A B H	SIZE ±0.02 0.02 A B H
SURFACES WITH BLENDED UNIFORMITY	ALL TRIM EDGES	CIRCULAR FEATURES	NON-CIRCULAR FEATURES

Dimension unit: [mm]			
Symbol	Min	Nom	Max
A	3.40	3.500	3.60
A1	-	0.050	-
b	0.50	0.600	0.70
b2	0.50	0.700	1.00
b3	0.80	0.900	1.00
c	0.40	0.500	0.60
c2	0.40	0.500	0.60
D	11.70	11.800	11.90
D1	8.90	8.955	9.10
E	13.90	14.000	14.10
E1	12.30	12.400	12.50
E2	7.75	7.800	7.85
E3	13.90	14.000	14.10
e		1.270 BSC	
H	18.00	18.580	19.00
L	2.40	2.523	2.60
L1	-	3.000	-
L2	0.90	1.000	1.10
L3		0.255 BSC	
L4	0.075	0.125	0.175
L5	1.83	1.930	2.03
aaa	-	0.100	-
N1	3.80	3.900	4.00
N2	0.25	0.300	0.35
N3	0.80	0.900	1.00
T	0.60	0.668	0.70
T2	9.33	9.378	9.43
Z	3.525	3.625	3.725

Recommended Solder Pad Layout

Note: All dimensions are in mm



SAPKG-9L

Ordering Information

Part number	AMS1200032V2-ASARR
Package	SAPKG-9L
Unit quantity	600 EA
Packing type	Tape & Reel

Important Notices – Read Carefully

Before you use our products, you are requested to carefully read this document and fully understand its contents. Sanan Semiconductor Co., Ltd. shall not be in any way responsible or liable for failure, malfunction or accident arising from the use of Sanan's products.

Sanan Semiconductor Datasheets are subject to change. Information presented in this document is from the characterization of engineering lots. Sanan Semiconductor Co., Ltd reserves the right to change limits, test conditions, and dimensions without notice. Information contained in this document are typical values and shall in no event be regarded as a guarantee of characteristics. With respect to any information regarding the application of the product, Sanan hereby disclaims all warranties and liabilities of any kind. The information in this document is exclusively for trained technical staff. It is the responsibility of the customer's technical department to decide the suitability of the product in the customer's application and Sanan Semiconductor Co., Ltd assumes no responsibility or liability whatsoever for the use of the information contained in this document.

In case there is any clause in this document or in any other documents which is contradictory to this clause, this clause shall prevail. This clause shall survive after termination of this document.

Warning

Due to technical requirements, Sanan's products may contain dangerous substances. For detailed information about the substance(s), please contact the Sanan office. Sanan Semiconductor Co., Ltd bears no responsibility for any damage whatsoever due to the substance(s) used in Sanan's products.

Contact info

Website: https://www.sanan-semiconductor.com/
https://www.sanan-semiconductor.com/en